### Index

**a**
- Abnormal discharge 401, 405, 406
- AC cathode 214, 217, 218
- Acryl 282, 283
- Active matrix organic light emitting diode (AMOLED) 13
  - manufacturing 137, 138
- TV 115
- Adobe RGB 43
- Advanced excimer laser anneal (AELA) 117, 118
- Air flow (clean rooms) 427, 428
- Air-guide BLU 111
- Air knife 301
- Air pollution and control 451
- AKT cluster PECVD 9
- Al alloy 195
- Alignment (Overlay) 293, 310
- Alignment layer 61
- AlNd alloy 201
- Al$_2$O$_3$ (alumina) 201
- Aluminium (Al) 209, 222, 232, 233
- Amorphous carbon (a-C) 271
- Amorphous silicon (a-Si) 13, 222, 253, 273, 276, 284
  - defects 274, 276
  - n’ doped 257
  - process 325
- TFT-LCD 13, 248
- Anisotropic conductive film (ACF) 75
  - attachment 76
- Anode 206, 227, 228, 231
  - PECVD 274, 275
- Anodized Al 281, 282
- AQUATRAN II 179
- Aristo PVD tool 225, 226
- Array process 394, 399, 402, 409
- Array test 353, 399, 410
- Automated ground vehicle (AGV) 422, 423, 424
- Automatic Optical inspection (AOI) 334, 379, 388

**b**
- Back channel etch (BCE) 23
- Backing plate 215, 216
- Backlight unit (BLU) 87
- Backplane 193
- Backplane metallization 225, 232
- Backside inspection 339
- Band gap 207
- Barix 170
- Barrier film 173
- Beveling 80
- Binning 97
- Black-matrix 44
- Black matrix (BM) patterning 303, 305
- BOE 7
- Bright shot panel failure 406
- BT.709 43
- Buffer layer 93, 271
- Buried particles (AOI) 332
- By-product 401, 405

**c**
- CAAC-IGZO 22
- Calcium test 180
- Capacitively coupled plasma (CCP) 273, 274, 275
- Capital investment 394
- Capture rate (AOI) 348
- Carbon black 47
- Carrier glass 174
- Cascade rinse 316, 317
- Cassette transportation system 420, 421, 423
Cathode, PECVD 274, 275
Ceiling height (clean rooms) 424, 425
Ceiling transportation system 422
Cell gap 401, 412
Cell process inspection 347
Charge generation layer (CGL) 152
Charge neutralizer 405
Cheese slab floor (clean rooms) 424
Chemical contamination 427, 431, 433
Chemical etching (dry) 323–325
Chemical life 317
Chemical vapor deposition (CVD) 395, 397, 401, 404
China Star Optoelectronics Technology (CSOT) 8
Chip on flex (COF) 73, 186, 198
  bonding 75, 77, 78
  replacement 389
Chip on glass (COG) 73
  bonding 81
Cholesteric liquid crystal film (CLCF) 108
CIE1931 41
CIE1976 41
Circular polarizer 186
Cleaning in-situ (PECVD) 274, 279, 280, 281
Cleanliness (clean rooms) 428, 433
Clean room 404, 405
Clean room design 423
Cluster 225
Cluster-type tool (equipment) 209, 212, 217, 219
CMOS process 27
Coating meniscus 291
Coefficient of thermal expansion (CTE) 175
  thermal expansion 202
Cold ablation repair 366, 376
Collision cascade 195
Color changing medium (CCM) 144
Color coordinate 41, 87
Color filter (CF) 39, 90, 153, 155
  patterning 287, 292, 303
Color filter on array (COA) 60
Color gamut 90
Color mixing 96
Color resist 289, 292, 305
Columnar 203
Column Spacer (CS) 46, 53
Computer-integrated manufacturing (CIM) 419, 423, 438
Computer simulation (clean rooms) 430, 431
Concentration management 317
Conflict minerals 446
Contact exposure 292, 297
Contact sensing 355
Contamination 289, 401, 409, 417
Continuous wave (CW) laser 117
Continuous wave laser crystallization (CLC) 117
Controlled super lateral growth (C-SLG) 120
Copper (Cu) 203
Corrosion 281
Cosmetic defect inspection 381
Cost competition 111
Cost of ownership (CoO) 211, 217
Coupling efficiency 88
Cover plastic window 188
Critical angle 98
Critical Dimension/Overlay (CD/O) 337, 349
Cross contamination 427
Cu alloys 209, 223, 224
Curing equipment 182
Cutting repair 367
Cylindrical rotating magnetron 229
d
Dam and fill 161, 166
Dangling bond 276
Data line 202
DC Cathode 210, 216, 217
Dead pixel (AOI) 333
Defect classification (AOI) 336
Defect detection sensitivity (AOI) 342, 344
Dehydration baking 289
Dehydrogenation 183, 260, 277
Deionized water (DIW) 289, 300
  consumption 315
Deposition rate 254
Device encapsulation 135
Diffuser 89, 106
Diffuser plate 110
Diffusion barrier layers 269
Diffusion path 169
Digital Cinema Initiative (DCI) 43
Digital mirror device (DMD) patterning 373
Dip etching 315, 316
Directional SLS (D-SLS) 120
Direct-lit BLU 87, 109
Dislocation density 92
Doctor blade roll 62
Double shielding method (double skinning) 433
Dow Corning OLED encapsulation 178
Downtime 395
Dry etching 319–325
DTI 2
Dual magnetron 236, 239
Dyad 176
Dye 49
Dynamic (in-line) magnetron sputtering layout 225
Dynamic Multi Cathode 216, 217
e
Edge-lit BLU 87
Edge Seal 161, 163
Electrical testing 352–353
Electricity delivery system (clean rooms) 437
Electroluminescent (EL) 90, 209
Electrostatic charging / discharging 405, 406
Electrostatic damage 404, 405
Emission control 452
Emission reduction 450
Encapsulation 135
End point detector (EPD) 323
End seal 67
Enhanced capacitive coupled plasma (ECCP) mode 322–326
Equipment cost 313
Etchability 237
Etch factor 313, 315
Etching 198
Etch stopper (ES) 24
European environmental regulations 445
Evaporation 196
Excimer laser 180
Excimer laser annealing (ELA) 17
Exposure image field 292
Exposure mask defects (AOI) 344
Exposure systems 287, 292
Extrusion 102

f
Fab layouts 5
Face seal 167
Fan filter unit (FFU) 420, 428, 431, 433
energy saving 433
Fast steering mirror (FSM) patterning 373
Field-effect-transistor 2
Fine metal mask (FMM) 116, 129, 133, 144
Flat panel display (FPD) 209, 212, 213
Flexible display 173
Flexible OLED 136, 137, 173
Flexible OLED deposition process 183
Flexible printed circuit (FPC) 73
Flexible printed circuit board (FPCB) 97
Flexible substrate 173
Flexible touch solution 181
Flip chip 96
Floor structure (clean rooms) 424
FOG bonding 82
Foldable display 177
Foldable OLED 187
Foreign particles (AOI) 331
Four-mask count process 24
Free-form panel testing 361
Fringe-field switching (FFS) 59
Frit sealing 135, 162, 164
Fuchs-Sondheimer model 197, 198
Full contact probing 354
Functional defects inspection 379
g
GaN 92
Gas delivery system (clean rooms) 436
Gas flow diffuser 245
Gate/data (G/D) short 201
Gate on array (GOA) testing 359
GE OLED encapsulation 178
Glass breakage defects 344
Glass breaking clipping (chipping) 401
Glass edge seal 163
Glass size generations 396
Glass substrate sizes 5
Glow discharge 227
Grain boundary 196
Grating floor (clean rooms) 424
Gray level difference (AOI) 342
Green building design 442
Green gap 92
Green house gas 448
Ground Strap 246

h
Half-tone exposure 53, 394
Half-tone photoresist process 325
Hardness 188
Hazardous substance management 444
H content 254, 268
Heat dissipation 95
Hexamethyldisilazane (HMDS) 289
Hexamethyldisiloxane (HMDSO) 271
High density plasma 275
High-power impulse magnetron sputtering (HiPIMS) 225
High temperature PI film 175
Hillock 198
Historic review 2
Hollow cathode effect 243
Hollow cathode gradient 244
Homeotropic 61
Homogeneous 61
Hot pixel (AOI) 333
Hot spot 88
Hybrid encapsulation 176, 177
Hydrogen 273, 274, 276, 277, 283
IBM Japan 2
i-Components i-Barrier 178
Impressio (TM) 322
Imprinting 103
In-cell touch panel inspection 345
Indium-gallium-zinc-oxide (IGZO) 14, 204, 210, 218, 223, 232, 234, 263, 276, 283, 319, 324
Indium Tin Oxide (ITO) 53, 202, 236, 304, 307
transparent films 238, 239
Indium Zinc Oxide (IZO) 53, 202, 237
Inductively coupled plasma (ICP) 275
mode 320, 321, 323–328
InGaN 92
Injection molding 101
Inline AOI 350
Inline processing 287, 301, 308
In-plane switching (IPS) 4, 9, 54, 59, 304
In-process quality control (IPQC) 416, 417
Input quality control (IQC) 407, 416
In situ chamber cleaning 395, 405
Inter layer dielectric (ILD) 199
Ion assist etch 324
Ion bombardment 227
Ionizer 405
Ions (dry etching) 320, 321
ISO50001 449
Isotropic etching 311, 313

IBM Japan 2
i-Components i-Barrier 178
Impressio (TM) 322
Imprinting 103
In-cell touch panel inspection 345
Indium-gallium-zinc-oxide (IGZO) 14, 204, 210, 218, 223, 232, 234, 263, 276, 283, 319, 324
Indium Tin Oxide (ITO) 53, 202, 236, 304, 307
transparent films 238, 239
Indium Zinc Oxide (IZO) 53, 202, 237
Inductively coupled plasma (ICP) 275
mode 320, 321, 323–328
InGaN 92
Injection molding 101
Inline AOI 350
Inline processing 287, 301, 308
In-plane switching (IPS) 4, 9, 54, 59, 304
In-process quality control (IPQC) 416, 417
Input quality control (IQC) 407, 416
In situ chamber cleaning 395, 405
Inter layer dielectric (ILD) 199
Ion assist etch 324
Ion bombardment 227
Ionizer 405
Ions (dry etching) 320, 321
ISO50001 449
Isotropic etching 311, 313

just noticeable difference (JND) 385
Lamination of OLED protection film 185
Laser ablation repair 365
Laser anneal 276, 277
Laser chemical vapor deposition (LCVD) repair 369
Laser cutting 389, 406
Laser CVD 406
Laser engraving 103
Laser-induced forward transfer (LIFT) repair 371
Laser lift-off (LLO) 180, 185
Light-emitting diode (LED) 87
package 95
Light extraction 94
Light extraction efficiency (LEE) 94
Light guide plate (LGP) 87, 98
Lightly doped drain (LDD) 28
Line defect locator (LDL) 375
Liquid crystal (LC)
alignment layer 59
cell fabrication 61, 399, 400, 402
drop filling process 5, 9, 10, 402, 404
filling process 65, 67, 68
Liquid crystal display (LCD) 13, 87, 209, 210, 218
cleanroom fab 419
desktop monitor 4
module assembly 84
TV 5
Liquid crystal module (LCM) 73, 88
defect repair 388
disassembly 391
optical film rework 391
Load lock chamber 322
Location controlled crystallization (LCC) 117
Low density plasma 273
Low pressure chemical vapor deposition (LPCVD) 16
Low temperature poly silicon (LTPS) 13, 16, 115, 116, 209, 213, 217, 221, 258, 320
LTPS TFT dry etch process 326
Luminance 87
Luminance uniformity 89
Luminous efficacy 90
Luminous flux 87
MacAdam ellipses 42
Magnetron cathode 227
Magnetron sputtering 210, 211, 212, 225
Magnet-wobble 230
Maintenance cycle 313, 315
Major milestones 9
Manufacturing process 447
Material hazard 446
Material types and uses 443
Mayadas and Schatzkes (MS) model 197
Mean time between failures (MTBF) 395
Mean time to repair (MTTR) 395
Mega‐trusses (clean rooms) 421
Metal can encapsulation 163
Metal frame 96
Metal‐induced crystallization (MIC) 17
Metal ink deposition repair 370
Metal layer repair 364
Metal oxide 225, 234, 263
Metal shadow mask 133, 134
Metrology 337, 349
Micro‐cavity effect (OLED) 129, 130
Microlens array (MLA) 104
Microstructure 196
Microwave‐type reactor 274, 275, 282
Mill base (MBS) 49
Mirror projection scan system 296
Mitsubishi X‐barrier 178
Mobility 253, 255
MOCON test 179
Module assembly (MA) 73, 399, 400
Moire formation 100
Mold frame 87
Molybdenum (Mo) 203, 233, 234
Momentum transfer 195
Motion picture quality 4
Moving cathode 219, 220, 221
Multi cathode 216, 217, 218
Multi‐layer optical film (MOF) 108
Multi lens projection 296
Multi magnet cathode 216, 218
Multi‐modality imaging (AOI) 341
Multi‐panel assignment 394
Mura defects 346, 359, 401, 402

n
Narrow bezel 89, 177
National Television System Committee (NTSC) 43
NEC 3
Negative photoresist 289, 292, 306
Neutral zone shifting 186
Nitrogen trifluoride (NF₃) 247
Nodule 207
Non‐reactive sputter processing 227
N/Si ratio 252
Numerical aperture 294, 296

O
O₂ ashing 302
Offline AOI 350
One drop filling (ODF) 67, 68, 394, 412
On‐the‐fly video grabbing (AOI) 340
Open cell 79
Open‐circuit repair 369
Open/short defect 401, 403, 409
O₂ plasma 302
Optical band gap 253
Optical Density (OD) 45, 305, 309
Optical film 87
Optically Clear Adhesive (OCA) 186
Optical pattern 88
Optical pattern design (BLU) 99
Optical simulation 100
Organic light emitting diode (OLED) 205, 219, 223, 269
deposition equipment 184
encapsulation 161
encapsulation:3M 178
manufacturing 129
yellow green stack 155
OS TFT 122
Outcoupling efficiency 94
Outgoing quality control (OQC) 416, 417
Overcoat (OC) 51, 149, 305
Overlay accuracy 292, 294
Oxide film 218, 223
Oxide semiconductor (OS) 14
Oxide TFT dry etching process 327
Oxygen vacancy 236, 267

p
Panel Defect 401
Panelization 394
Panel signal driving (testing) 353
Panel test 399, 400, 401, 402
PAN etch solution 198
Particle contamination 422
Particle defects (PECVD) 279, 280, 281, 282, 284
Pass‐by 212, 214, 219
Pattern defects 329, 401
Patterned sapphire substrate 95
Patterning 288, 292, 303
PCBA repair 390
<table>
<thead>
<tr>
<th>Term</th>
<th>Page(s)</th>
</tr>
</thead>
<tbody>
<tr>
<td>Peripheral inspection</td>
<td>346</td>
</tr>
<tr>
<td>PET film</td>
<td>104</td>
</tr>
<tr>
<td>Phase modulated excimer laser anneal (PM-ELA)</td>
<td>117</td>
</tr>
<tr>
<td>Phosphor</td>
<td>90</td>
</tr>
<tr>
<td>Photo-Acryl Compound (PAC)</td>
<td>56</td>
</tr>
<tr>
<td>Photo-alignment</td>
<td>64, 65</td>
</tr>
<tr>
<td>Photochemical ablation repair</td>
<td>366</td>
</tr>
<tr>
<td>Photochemistry</td>
<td>292</td>
</tr>
<tr>
<td>Photodecomposition</td>
<td>65, 66</td>
</tr>
<tr>
<td>Photodimerization</td>
<td>65, 66</td>
</tr>
<tr>
<td>Photoisomerization</td>
<td>65, 66</td>
</tr>
<tr>
<td>Photolithography</td>
<td>287</td>
</tr>
<tr>
<td>resolution</td>
<td>292, 309</td>
</tr>
<tr>
<td>Photo mask</td>
<td>288, 292</td>
</tr>
<tr>
<td>Positive photoresist</td>
<td>289, 292, 301</td>
</tr>
<tr>
<td>Precursor</td>
<td>260</td>
</tr>
<tr>
<td>Precursor dissociation</td>
<td>273, 275</td>
</tr>
<tr>
<td>Pressure sensitive adhesive (PSA)</td>
<td>178</td>
</tr>
<tr>
<td>Pre-tilt</td>
<td>61, 65</td>
</tr>
<tr>
<td>Printed circuit board assembly (PCBA)</td>
<td>388</td>
</tr>
<tr>
<td>Printed circuit board (PCB) bonding</td>
<td>79</td>
</tr>
<tr>
<td>Prism film</td>
<td>89, 107</td>
</tr>
<tr>
<td>Process capability index Cpk</td>
<td>409, 417</td>
</tr>
<tr>
<td>Process chamber</td>
<td>405</td>
</tr>
<tr>
<td>Process chamber (etching)</td>
<td>322</td>
</tr>
<tr>
<td>Process window</td>
<td>404</td>
</tr>
<tr>
<td>Process yield</td>
<td>399, 404, 406</td>
</tr>
<tr>
<td>Production control system</td>
<td>437</td>
</tr>
<tr>
<td>Productivity</td>
<td>292, 392, 397, 399</td>
</tr>
<tr>
<td>Productivity enhancement</td>
<td>5</td>
</tr>
<tr>
<td>Productivity-to-investment factor</td>
<td>397, 399</td>
</tr>
<tr>
<td>Projection exposure</td>
<td>292, 293</td>
</tr>
<tr>
<td>Projection scanning exposure system</td>
<td>294, 295</td>
</tr>
<tr>
<td>Protection film</td>
<td>89</td>
</tr>
<tr>
<td>Proximity exposure</td>
<td>287, 297</td>
</tr>
<tr>
<td>q</td>
<td></td>
</tr>
<tr>
<td>Quality control</td>
<td>393, 399, 406, 413, 416</td>
</tr>
<tr>
<td>Quantum dot (QD) film</td>
<td>108</td>
</tr>
<tr>
<td>Quantum efficiency</td>
<td>92</td>
</tr>
<tr>
<td>Quantum well</td>
<td>93</td>
</tr>
<tr>
<td>Quick rinse system</td>
<td>317, 318</td>
</tr>
<tr>
<td>r</td>
<td></td>
</tr>
<tr>
<td>Racetrack</td>
<td>227</td>
</tr>
<tr>
<td>Radiative recombination</td>
<td>93</td>
</tr>
<tr>
<td>Radical</td>
<td>321, 322</td>
</tr>
<tr>
<td>Railed ground vehicle (RGV)</td>
<td>422, 423</td>
</tr>
<tr>
<td>Raised floor (clean rooms)</td>
<td>424</td>
</tr>
<tr>
<td>Random failure</td>
<td>401</td>
</tr>
<tr>
<td>Rank mixing</td>
<td>97</td>
</tr>
<tr>
<td>Ray-tracing</td>
<td>100</td>
</tr>
<tr>
<td>RC delay</td>
<td>194</td>
</tr>
<tr>
<td>Reactive ion etching (RIE) mode</td>
<td>320, 321, 324–326</td>
</tr>
<tr>
<td>Reactive sputter</td>
<td>218, 223</td>
</tr>
<tr>
<td>Reactive sputter processing</td>
<td>227</td>
</tr>
<tr>
<td>Recrystallization</td>
<td>196</td>
</tr>
<tr>
<td>Re-deposition</td>
<td>228, 229</td>
</tr>
<tr>
<td>Reflection film</td>
<td>89</td>
</tr>
<tr>
<td>Reflective polarizer</td>
<td>108</td>
</tr>
<tr>
<td>Reflective polarizer detach</td>
<td>107</td>
</tr>
<tr>
<td>Remote plasma</td>
<td>279, 281</td>
</tr>
<tr>
<td>Remote plasma cleaning</td>
<td>405</td>
</tr>
</tbody>
</table>

Pigment 49
PiVot 225, 226, 230
Pixel defect 401, 406
Pixel patterning 133
Planar (magnetron sputter) 210, 211, 216, 218
Planar cathodes 227, 228
Planarization 51
Plasma 195
Plasma density 273, 274
Plasma enhanced chemical vapor deposition (PECVD) 15, 241, 273, 279
Precursors 273, 276, 279
Plasma etching (PE) mode 320, 321, 324–326
Plasma potential 274275
Plasma treatment 149
PMOS process 27, 28
Polarization recycling 108
Polarized UV light 65
Polarizer attachment 69, 81
Polarizer detach 390
Polycarbonate (PC) 100
Polyimide (PI) 61, 175
coating and curing 181, 399, 402, 405
rubbing 402
Poly(methyl methacrylate) (PMMA) 98
Poly-Si 16
Polyvinyl alcohol (PVA) 4, 9
Poor coating defects (AOI) 344
Positive photoresist 289, 292, 301
Precursor 260
Precursor dissociation 273, 275
Pressure sensitive adhesive (PSA) 178
Pre-tilt 61, 65
Printed circuit board assembly (PCBA) 388
Printed circuit board (PCB) bonding 79
Prism film 89, 107
Process capability index Cpk 409, 417
Process chamber 405
Process chamber (etching) 322
Process window 404
Process yield 399, 404, 406
Production control system 437
Productivity 292, 392, 397, 399
Productivity enhancement 5
Productivity-to-investment factor 397, 399
Projection exposure 292, 293
Projection scanning exposure system 294, 295
Protection film 89
Proximity exposure 287, 297

q
Quality control 393, 399, 406, 413, 416
Quantum dot (QD) film 108
Quantum efficiency 92
Quantum well 93
Quick rinse system 317, 318

r
Racetrack 227
Radiative recombination 93
 Radical 321, 322
Railed ground vehicle (RGV) 422, 423
Raised floor (clean rooms) 424
Random failure 401
Rank mixing 97
Ray-tracing 100
RC delay 194
Reactive ion etching (RIE) mode 320, 321, 324–326
Reactive sputter 218, 223
Reactive sputter processing 227
Recrystallization 196
Re-deposition 228, 229
Reflection film 89
Reflective polarizer 108
Reflective polarizer detach 107
Remote plasma 279, 281
Remote plasma cleaning 405
Remote plasma source cleaning (RPSC) 247
Repairing 399, 404, 406, 409, 412, 415
Resin 96
Resistance (thin film properties) 209, 221, 222, 223
Resistivity 193, 258
Resonant cavity LED 95
Reticle 294
Return shaft (clean rooms) 427
Review image grabbing (AOI) 337, 340
Rework 406, 408
RF 210, 274, 275, 281, 284
RGBW 55
Roll printing 62
Roll stamping 103
Roll-to-roll processing 106
Roof-transportation (clean rooms) 420
Rotary Cathode (Magnetron Sputter) 211, 218, 225
Rotary cathode array 230
Rubbing alignment 61
Rubbing depth 63
Rubbing process 63
Running cost 311, 315, 317, 318

S
Sacrificial layer 180
Sapphire substrate 92
Saving of chemicals 436
Scattering 197
Screen printing 102
Sealant 59
Secondary electrons 227
Selective detection control (AOI) 344
Semi knock down (SKD) 79
Separated circulation (clean rooms) 427
Sequential lateral solidification (SLS) 117, 120
Sheet resistance 194
Short bar probing 354
Short-circuit repair 365
Sideways Static Deposition Method (PVD) 212
Signal driving probing 357
Si-H content 252
SiH, SiH₂, SiH₃, SiH₄ 273, 274, 276, 278, 280
Silicone dispensing 78
Silicon nitride (SiNx) dielectric film 248, 269, 276
Silicon oxide (SiOx) dielectric film 259, 265, 276, 279, 282, 284
Silver nanowire 188
Single cathode 216
Single plate processing 394
Slit coating photolithography 25
Slit die coating 287, 290, 307
Small mask scanning (SMS) 145
Small panel JI process 80
Solid state laser 180
Source/drain layer testing 362
Spin coating 290, 291
Sputtering 195
Sputter yield 227
sRGB 43
Static (in-line or cluster) magnetron sputtering layout 225
Stepper 287, 293
Structure zone model 196
Stuck pixel (AOI) 333
Sub-fab (clean rooms) 420, 424
Substrate proximity handling 405
Super lateral growth (SLG) 20
Surface mounting technology (SMT) 97
Surface particles (AOI) 332
Susceptor 245
Symmorphix OLED encapsulation 178
Systematic failure 401
System on panel (SOP) 32

T
Tact time 314
Tape-automated bonding (TAB) connection 73, 402, 408, 413
Terra barrier 179
Tetraethylorthosilicate (TEOS) 276, 279
Tetramethyl ammonium hydroxide (TMAH) 289, 301
TFT-LCD plant 419, 423, 427, 437
Thermal ablation repair 366
Thermal evaporation 129
Thin film deposition 273, 282
Thin film encapsulation (TFE) 136, 168, 176, 185, 269
Thin-film transistor (TFT) 2, 39, 209, 215, 218, 221, 287, 292, 303
array repair 363
backplane 115, 173
cable layer 273
coplanar P-channel 117
five-mask structure 26
gate insulator 273, 279, 283, 284
history 2
insulated-gate 2
inverted staggered 2
passivation 234, 275, 276, 282
Threshold voltage (Vth) 283, 284, 285
Throughput 292, 296, 394, 397, 399
Ti/Al/Ti stack 206
Tilted transferring system 315, 316
Time constant 194
Ti-silicide 204
Titanium dioxide (TiO_2) 204
Titanium nitride (TiN) 204
Top emission OLED structure 130, 131, 132
Toshiba 2
Total circulation (clean rooms) 427
Total internal reflection (TIR) 98
Transfer chamber (etch) 322
Transparent conductive oxide (TCO) 206
Transparent oxide (TOS) 209, 210, 218, 219, 221
Turn-around time (TAT) 423
Twisted nematic (TN) 54, 59, 304
Two shot sequential lateral solidification (TS-SLS) 33, 120

U
Ultra-clean room 419
Ultra-high-resolution testing 357
Ultra low penetration air (ULPA) 420
Uniformity 394, 397, 401, 404, 412
University of Colorado OLED encapsulation 178
Uptime 395
Utilization 395
UV glue dispense 83
UV irradiation 287
UV LED 90

V
Vertical alignment (VA) 4, 9, 55, 304, 307
Vertical cluster or equipment 209, 213, 214, 215, 217, 219
Visual inspection 383, 384
Visual testing environment 385
Visual test patterns 387
Vitex 170
Vitex OLED encapsulation 176
Vitriflex OLED encapsulation 179
Volatile organic compounds (VOC) 451
Voltage image optical system (VIOS) 355

W
Waku (backlight light leakage) 386
Waste recycling and reuse 453
Water management 452
Water recycling 434
Water vapor transmission rate (WVTR) 135, 160, 176, 269, 282
Welding repair 368
Wet etch rate 253
White LED 90, 147
White OLED
one-stacked 149, 150
two-stacked 152, 153
three-stacked 155
Wide viewing angle 4, 9
Wire grid polarizer (WGP) 108
Work function 206
Work in process (WIP) 395

Y
Yield 393, 399, 403, 406, 413, 416
Yield optimization 395, 404
Young’s modulus 200